

GLASS SUBSTRATE FOR SEMICONDUCTOR DEVICE COMPONENT AND
PROCESS FOR PRODUCING GLASS SUBSTRATE FOR SEMICONDUCTOR
DEVICE COMPONENT

ABSTRACT

It is an object of the present invention to provide a glass substrate having plural through-holes which is not likely to peel from a silicon wafer, even though laminated on and jointed to a the silicon wafer and then subjected to heat treatment.

- 5 The above object is accomplished by a glass substrate having an average thermal expansion coefficient of from 10×10^{-7} to $50 \times 10^{-7}/K$ within a range of from $50^{\circ}C$ to $300^{\circ}C$, having plural through-holes with a taper angle of from 0.1 to 20° and having a thickness of from 0.01 to 5 mm.

Fig. 1